

Silicon PNP Power Transistors

2SB761 2SB761A

DESCRIPTION

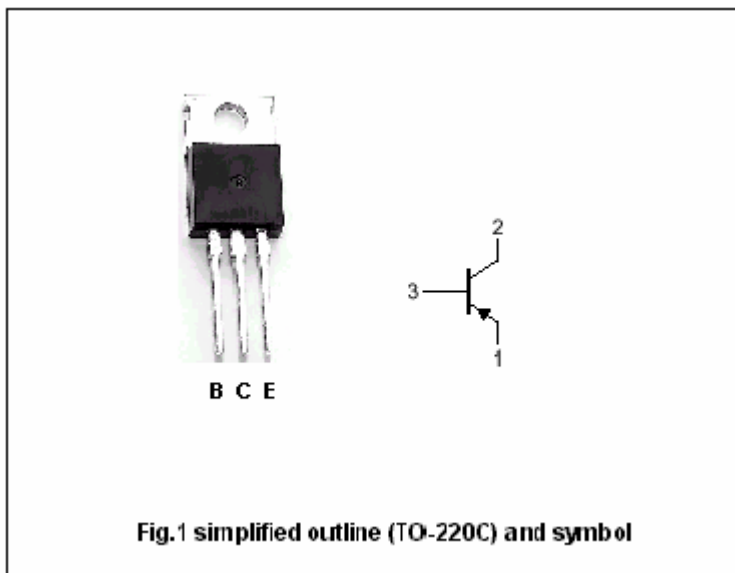
- With TO-220C package
- Complement to type 2SD856/856A
- Low collector saturation voltage

APPLICATIONS

- For audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SB761	-60	V
		2SB761A	-80	
V <sub>CEO</sub>	Collector-emitter voltage	2SB761	-60	V
		2SB761A	-80	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-3	A
I <sub>CM</sub>	Collector current-peak		-5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	35	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO</sub>	Collector-emitter breakdown voltage	2SB761	I <sub>C</sub> =-30mA; I <sub>B</sub> =0	-60			V
		2SB761A		-80			
V <sub>CEsat</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =-3 A; I <sub>B</sub> =-0.375 A			-1.2	V
V <sub>BE</sub>	Base-emitter on voltage		I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V			-1.8	V
I <sub>CES</sub>	Collector cut-off current	2SB761	V <sub>CE</sub> =-60V; V <sub>BE</sub> =0			-200	μA
		2SB761A	V <sub>CE</sub> =-80V; V <sub>BE</sub> =0				
I <sub>CEO</sub>	Collector cut-off current		V <sub>CE</sub> =-60V; I <sub>B</sub> =0			-300	μA
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-1	mA
h <sub>FE-1</sub>	DC current gain		I <sub>C</sub> =-1A ; V <sub>CE</sub> =-4V	40		250	
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V	10			

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =-1A ; I <sub>B1</sub> =-I <sub>B2</sub> =-0.1 A		0.5		μs
t <sub>off</sub>	Turn-off time			2.0		μs

◆ h<sub>FE-1</sub> classifications

R	Q	P
40-90	70-150	120-250

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PACKAGE OUTLINE

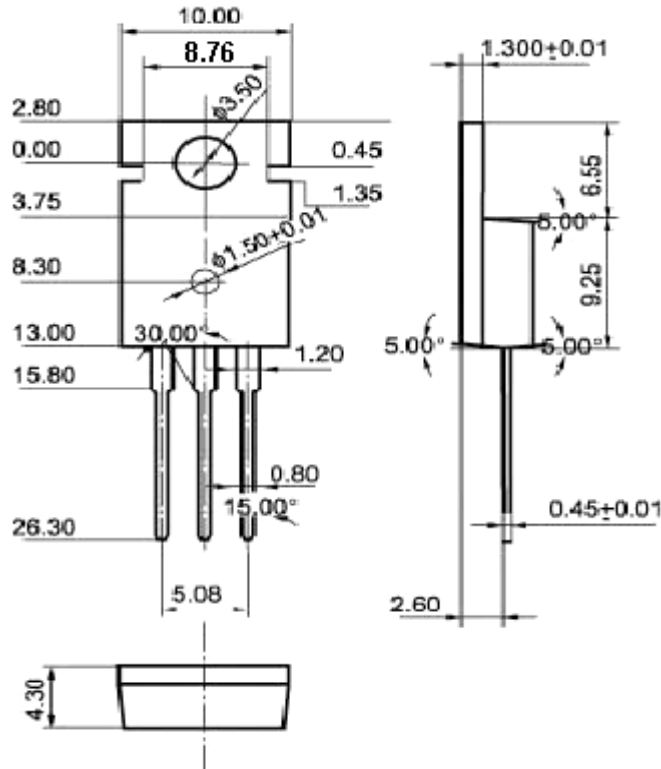


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)